

Attorney's Docket No.: 07977/270001

In the claims:

Please amend the claims as follows:

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1. (Currently amended) A plasma CVD apparatus comprising:  
a vacuum chamber;  
~~an introducing means for introducing a gas into the vacuum~~  
~~chamber;~~  
an exhaust means for exhausting the gas from the vacuum  
chamber to an outside;  
an electrode for supplying an electric energy inside the  
vacuum chamber;  
a supporting means for supporting a substrate opposing the  
electrode, having side surfaces towards a periphery, and a  
center part between said side surfaces;  
~~wherein~~ an introducing port for gas, ~~is~~ located adjacent to  
at least one of an electrode said side surfaces of the  
substrate;  
wherein a plurality of openings are located on a surface of  
the electrode opposing the substrate,  
wherein the gas is exhausted from the plurality of openings  
to the outside of the vacuum chamber.

2. (Original) An apparatus according to claim 1, further  
comprising:

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a transporting means for transporting continuously a flexible substrate.

3. (Original) An apparatus according to claim 1, wherein each of the plurality of openings is circular, wherein the plurality of openings are located on the surface of the electrode at constant intervals.

4. (Original) An apparatus according to claim 1, wherein the electrode is a mesh-like plate.

5. (Cancelled)

6. (Previously added) An apparatus according to claim 1 further comprising:

a second electrode opposing the first electrode for supplying the electric energy inside the vacuum chamber.

7. (Previously added) An apparatus according to claim 6, wherein the substrate is supported between the first and second electrodes by the supporting means.

8. (Previously added) An apparatus according to claim 2,

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wherein the transporting means includes at least one selected from the group consisting of an unwinding roll and a winding roll.

9. (Previously added) The apparatus according to claim 1 wherein said substrate is located horizontally and said surface downward to the electrode.

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10. (Previously added) An apparatus comprising:  
a chamber;  
a first electrode in the chamber;  
a second electrode in the chamber;  
a substrate holder to hold a substrate between the first and second electrode;  
at least one gas inlet port to introduce a gas to a space between the substrate and the second electrode; and  
a plurality of gas exhaust ports provided in said second electrode through which said gas is exhausted from said space.

11. (Previously added) The apparatus according to claim 10 wherein said first electrode is grounded.

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12. (Previously added) The apparatus according to claim 10 wherein said second electrode is located below said first electrode.

13. (Previously added) The apparatus according to claim 10 wherein said apparatus is a film formation apparatus.

14. (Previously added) The apparatus according to claim 10 wherein said gas inlet port is located in a position between the substrate and the second electrode.

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15. (Previously added) A method comprising:

providing a first electrode and a second electrode opposed to said first electrode in a chamber wherein said second electrode is provided with a plurality of openings;

disposing a substrate between said first electrode and said second electrode;

introducing a gas into said chamber through a gas introducing port;

applying an electrical energy between the first and second electrodes to produce a plasma of said gas; and

exhausting said gas from said chamber through said plurality of openings of the second electrode.

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16. The method according to claim 15 further comprising a step of moving said substrate with respect to said first and second electrodes during the application of said electrical energy.

17. (Previously added) The method according to claim 15 wherein said second electrode is located below said first electrode.

18. (Previously added) The method according to claim 15 wherein said gas introducing port is located in a position between the substrate and the second electrode.

19. (Previously added) The method according to claim 15 further comprising a step of forming a film on said substrate by plasma CVD from said plasma.